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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 290836US2PCT		SERIAL NO. New U.S. PCT Application Based on PCT/JP04/18525	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yongxun LIU, et al.			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES      NO		
↓ /LPC/	AO	2003-163356	06/06/03	JP (with English abstract, Computer generated translation & equivalent of US6492212)		NO	
	AP	10-256560	09/25/98	JP (with English abstract & Computer generated translation)		NO	
	AQ	2000-340795	12/08/00	JP (with English abstract & Computer generated translation)		NO	
	AR	2002-16255	01/18/02	JP (with English abstract & Computer generated translation)		NO	
	AS	2-15675	01/19/90	JP (with English abstract)		NO	
	AT	2002-270850	09/20/02	JP (with English abstract & Computer generated translation)		NO	
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
↓ /LPC/	AW	SUZUKI, Kunihiro et al., "Analytical Models for n+ -p+ Double-Gate SOI MOSFET's", IEEE Transactions on Electron Devices, Vol. 42, No. 11, Pages 1940-1948, 1995.					
	AX						
	AY						
	AZ						<input type="checkbox"/> Additional References sheet(s) attached
Examiner / Leslie Pilar Cruz/					Date Considered 11/10/2008		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							